## ENGINEERS ACADEMY

## Question Bank

1. Figure shows as electronic voltage regulator the zener diode may be assumed to require a minimum current of 25 mA for satisfactory operations. The value of R required for satisfactory voltage regulation of the circuit is

2. The 6 V Zener diode shown in fig has zero Zener resistance and a Knee current of 5 mA . The minimum value of R so that the voltage across it does not fall bellow 6 V is.

(a) 1.2 K ohms
(b) 80 ohms
(c) 50 ohms
(d) 0 ohms
3. The wave shape of $\mathrm{V}_{0}$ in Fig. is

(a)

(b)

(c)

(d)

4. The Zener diode in the circuit shown in the figure has a Knee current of 5 mA , and a maximum allowed power dissipation of 300 mW . What are the minimum and maximum load currents that can be drawn safely from the circuit, keeping the output voltage $\mathrm{V}_{0}$ constant at 6 V ?

(a) $0 \mathrm{~mA}, 180 \mathrm{~mA}$
(b) $5 \mathrm{~mA}, 110 \mathrm{~mA}$
(c) $10 \mathrm{~mA}, 55 \mathrm{~mA}$
(d) $60 \mathrm{~mA}, 180 \mathrm{~mA}$
5. For full wave rectification, a four diode bridge rectifier is claimed to have the following advantages over a two diode circuit.
6. Less Expensive transformer
7. Smaller size transformer and
8. Suitability for higher voltage application of these
(a) only (1) and (2) are true
(b) only (1) and (3) are true
(c) only (2) and (3) are true
(d) (1), (2), as well as (3) are true

Email: info@engineersacademy.org Website : www.engineersacademy.org
6. A dc power supply has a No-load voltage of 30 V and a full-load voltage of 25 V at a full-load current of 1 A . The output resistance and load regulation, respectively are
(a) $5 \Omega$ and $20 \%$
(b) $25 \Omega$ and $20 \%$
(c) $5 \Omega$ and $16.7 \%$
(d) $25 \Omega$ and $16.7 \%$
7. The mobility of an electron in a conductor expressed in terms of
(a) $\mathrm{Cm}^{2} / \mathrm{V}-\mathrm{sec}$
(b) $\mathrm{Cm} / \mathrm{V}-\mathrm{sec}$
(c) $\mathrm{Cm}^{2} / \mathrm{V}$
(d) $\mathrm{Cm}^{2} / \mathrm{sec}$
8. As temperature is increased, the voltage across a diode carrying a constant current.
(a) Increases
(b) Decreases
(c) Remains Constant
(d) May increase or decrease depending upon the doping levels in the junction
9. In a single-stage differential amplifier, the output offset voltage is basically dependent on the mismatch of
(a) $\mathrm{V}_{\mathrm{BE}}, \mathrm{I}_{\mathrm{B}}$ and $\beta$
(b) $V_{B E}$ and $I_{B}$
(c) $I_{B}$ and $\beta$
(d) $V_{B E}$ and $\beta$
10. The input resistance of a common emitter stage can be increased by

1. un-bypass emitter resistance
2. bootstrapping
3. biasing it at low quiescent current
4. using compounded BJTs

The correct sequence in descending order of the effectiveness of these methods is
(a) $2,4,1,3$
(b) $4,3,2,1$
(c) $2,4,3,1$
(d) $4,2,3,1$
11. The diode ' $D$ ' is ideal in the network shown in the given figure. The current ' $I$ ' will be

(a) -mA
(b) zero
(c) 2 mA
(d) 4 mA
12. The transfer characteristic of the network shown in the given figure is represented as

(a)

(b)

(c)

(d)


ENGINEERS ACADEMY
Your GATEway to Professional Excellence IES \& GATE \& PSUS \& JTO * IAS \& NET
13. A diode whose terminal characteristics are related as $i_{D}=I_{S} e^{\frac{V}{V_{T}}}$, where $I s$ is the reverse saturation current and $\mathrm{V}_{\mathrm{T}}$ is thermal voltage $(=25 \mathrm{mV})$ is biased at $\mathrm{i}_{\mathrm{D}}=2 \mathrm{~mA}$. Its dynamic resistance is $\qquad$
(a) $25 \Omega$
(b) $12.5 \Omega$
(c) $50 \Omega$
(d) $100 \Omega$
14. Consider the following rectifier circuits:

1. Half-wave rectifier without filter.
2. Full-wave rectifier without filter.
3. Full-wave rectifier with series inductance filter.
4. Full-wave rectifier with capacitance filter.

The sequence of these rectifier circuits in decreasing order of their ripple factor is
(a) $1,2,3,4$
(b) $3,4,1,2$
(c) $1,4,3,2$
(d) $3,2,1,4$
15. The transistor shunt regulator shown in the figure has a regulated output voltage of 10 V . The input varies from 20 V to 30 V . The relevant parameters for Zener diode and the transistor are :
$\mathrm{V}_{\mathrm{z}}=9.5 \mathrm{~V}, \mathrm{~V}_{\mathrm{BE}}=0.3 \mathrm{~V}, \beta=99$.
Neglect the current through $\mathrm{R}_{\mathrm{B}}$. Then the maximum power dissipated in the Zener diode $\left(\mathrm{P}_{\mathrm{Z}}\right)$ and the transistor $\left(\mathrm{P}_{\mathrm{T}}\right)$ are

(a) $\mathrm{P}_{\mathrm{Z}}=75 \mathrm{~mW}, \mathrm{P}_{\mathrm{T}}=7.9 \mathrm{~W}$
(b) $\mathrm{P}_{\mathrm{Z}}=85 \mathrm{~mW}, \mathrm{P}_{\mathrm{T}}=8.9 \mathrm{~W}$
(c) $\mathrm{P}_{\mathrm{Z}}=95 \mathrm{~mW}, \mathrm{P}_{\mathrm{T}}=9.9 \mathrm{~W}$
(d) $\mathrm{P}_{\mathrm{Z}}=115 \mathrm{~mW}, \mathrm{P}_{\mathrm{T}}=11.9 \mathrm{~W}$
16. The use of a rectifier filter in a capacitor circuit gives satisfactory performance only when the load
(a) current is high
(b) current is low
(c) voltage is high
(d) voltage is low
17. Assertion (A): In avalanche breakdown, the reverse current sharply increases with voltage due to field emission.
Reason (R): The field emission requires highly doped ' p ' and ' $n$ ' regions.
(a) Both A and R are true and R is the correct explanation of A
(b) Both A and R are true but R is NOT the correct explanation of A
(c) A is true but R is false
(d) A is false but R is true
18. Assertion (A): In small signal class ' A ' amplifier, the output is a magnified replica of the input without any change in frequency.
Reason (R): The dc operating point is fixed in class 'A' position.
(a) Both A and R are true and R is the correct explanation of A
(b) Both A and R are true but R is NOT the correct explanation of $A$
(c) A is true but R is false
(d) A is false but R is true
19. In a forward biased photo diode, an increase in incident light intensity causes the diode current to
(a) increase
(b) remain constant
(c) decrease
(d) remain constant while the voltage drop across the diode increases
20. A Zener diode has a Zener resistance of $5 \Omega$. If the current through the Zener diode changes from 10 mA to 20 mA , the change of voltage across the Zener diode will be
(a) 0.05 v
(b) 0.075 v
(c) 0.1 v
(d) 0.5 v
21. A peak detector comprises a capacitor and an ideal diode and an ac source in series . The following is true the circuit.
(a) The instantaneous current depends only on the instantaneous source voltage
(b) The diode voltage is always zero
(c) The instantaneous current depends only on the diode
(d) The energy stored in the capacitor can never decrease with time.
22. Choose the incorrect answer Given the diode cut in voltage $\mathrm{V}_{\mathrm{D}}=0.6 \mathrm{~V}$

(a) For $0 \leq \mathrm{V}_{1} \leq 3.5 \mathrm{~V}, \mathrm{~V}_{0}=4.4 \mathrm{~V}$
(b) For $\mathrm{V}_{\mathrm{i}} \geq 3.8 \mathrm{~V}, \mathrm{D}_{2}$ turns ON
(c) For $\mathrm{V}_{\mathrm{i}} \geq 3.5 \mathrm{~V}, \mathrm{D}_{2}$ turns OFF
(d) $\mathrm{V}_{\mathrm{i}} \geq 9.4 \mathrm{~V}, \mathrm{~V}_{0}=10 \mathrm{~V}$
23. A Zener diode Regulator in the figure is to be designed to meet the specifications:
$\mathrm{I}_{\mathrm{L}}=10 \mathrm{~mA}, \mathrm{~V}_{0}=10 \mathrm{~V}$ and $\mathrm{V}_{\text {in }}$ varies from 30 V to 50 V . The Zener diode has $\mathrm{V}_{\mathrm{z}}=10 \mathrm{~V}$ and $\mathrm{I}_{\mathrm{ZK}}$ (Knee current) $=1 \mathrm{~mA}$. For satisfactory operation.

(a) $\mathrm{R} \leq 1800 \Omega$
(b) $2000 \Omega \leq \mathrm{R} \leq 2200 \Omega$
(c) $3700 \Omega \leq \mathrm{R} \leq 4000 \Omega$
(d) $\mathrm{R}>4000 \Omega$
24. The cutin voltage of both zener diode $D_{z}$ and $D$ shown in Figure is 0.7 V , while breakdown voltage of the zener is 3.3 V and reverse break down of D is 50 V . The other parameters can be assumed to be the same as those of an ideal diode. The values of the peak output voltage $\left(\mathrm{V}_{0}\right)$ are

(a) 3.3 V in the positive half cycle and 1.4 V in the negative half cycle.
(b) 4 V in the positive half cycle and 5 V in the negative half cycle.
(c) 3.3 V in the both positive and negative half cycle.
(d) 4 V in the both positive and negative half cycle.
25. The forward resistance of the diode shown in figure is $5 \Omega$ and the remaining parameters are same as those of ideal diode. The DC component of the source current is

(a) $\frac{V_{m}}{50 \pi}$
(b) $\frac{\mathrm{V}_{\mathrm{m}}}{50 \pi \sqrt{2}}$
(c) $\frac{\mathrm{V}_{\mathrm{m}}}{100 \pi \sqrt{2}}$
(d) $\frac{\mathrm{V}_{\mathrm{m}}}{50 \pi}$
26. In the single phase diode bridge rectifier shown in figure, the load resistor is $\mathrm{R}=50 \Omega$. The source voltage is $V=200 \sin \omega t$, where $\omega=2 \pi \times 50 \mathrm{rad} / \mathrm{sec}$. The power dissipated in the load resistor R is

(a) $\frac{3200 \mathrm{~W}}{\pi}$
(b) 400 W
(c) $\frac{400 \mathrm{~W}}{\pi}$
(d) 800 W
27. The junction capacitance of linearly graded junction varies with the applied reverse bias $\mathrm{V}_{\mathrm{r}}$ as
(a) $V_{r}^{-1}$
(b) $\mathrm{V}_{\mathrm{r}}^{-1 / 2}$
(c) $\mathrm{V}_{\mathrm{r}}^{-1 / 3}$
(d) $\mathrm{V}_{\mathrm{r}}^{1 / 2}$
28. The power input to an amplifier is $2 \mu \mathrm{~W}$. The power gain of the amplifier is 40 dB . The output power of the amplifier is
(a) $80 \mu \mathrm{~W}$
(b) $200 \mu \mathrm{~W}$
(c) 20 mW
(d) 80 mW
29. Given below are 2 sets of diagram - one set shows 4 circuits with inputs; the other shows the output $\left(\mathrm{V}_{0}\right)$. Match List-I (Inputs) with ListII (Outputs) and select the correct answer using the codes given below the lists:
List-1
A.


4.

Codes:

| s: | A | B | C | D |
| :--- | :--- | :--- | :--- | :--- |
| (a) | 1 | 3 | 2 | 4 |
| (b) | 2 | 3 | 1 | 4 |
| (c) | 1 | 4 | 2 | 3 |
| (d) | 2 | 4 | 1 | 3 |

30. The circuit shown in figure is best described as a

(a) bridge Rectifier
(b) Ring Modulator
(c) frequency discriminator
(d) Voltage doubler

Email:info@engineersacademy.org Website : www.engineersacademy.org
31. A voltage signal $10 \sin \cot$ is applied to the circuit with ideal diodes as shown in figure. The max and minimum values of the output waveform of the circuit are respectively

(a) +10 V and -10 V
(b) +4 V and -4 V
(c) +7 V and -4 V
(d) +4 V and -7 V
32. Consider the following statements in respect of a transistor R-C coupled amplifier:

1. The low frequency response is determined by the transistor junction capacitors.
2. The high frequency response is limited by coupling capacitors,
3. The Miller capacitance reduces the gain at high frequencies.
4. As the gain is increased the bandwidth gets reduced.

Which of these statements are correct?
(a) 1 and 2
(b) 2 and 3
(c) 3 and 4
(d) 1 and 4
33. Match List-I (Circuit Name) with List-II (Characteristics) and select the correct answer using the codes given below the lists:

## List-I

A. Schmitt trigger
B. Monostable multivibrator
C. Astable multivibrator
D. Blocking oscillator

## List-II

1. It needs a pulse transformer
2. It is used to generate gating pulse whose width can be controlled
3. It is a bistable circuit
4. It has no stable state Codes:

| Codes: | A | B | C | D |
| ---: | :--- | :--- | :--- | :--- |
| (a) | 3 | 2 | 4 | 1 |
| (b) | 2 | 3 | 1 | 4 |
| (c) | 3 | 2 | 1 | 4 |
| (d) | 2 | 3 | 4 | 1 |

34. Match List-I (Circuits) with List-II (Characteristics/Application) and select the correct answer.

List-I
A. High-pass RC circuit 1. Comparator
B. Low-pass RC circuit 2
C. Clamping circuit
D. Clipping circuit

Codes:

| : | A | B | C | D |
| :--- | :--- | :--- | :--- | :--- |
| (a) | 5 | 4 | 2 | 1 |
| (b) | 4 | 3 | 1 | 2 |
| (c) | 5 | 4 | 1 | 2 |
| (d) | 4 | 3 | 2 | 1 |

35. Assertion (A): A clipper circuit can be realized using two biased diodes in shunt.
Reason (R): A clipper circuit slices the input waveform between two preset voltage levels.
(a) Both A and R are individually true and R is the correct explanation of $A$.
(b) Both A and R are individually true and R is not the correct explanation of A .
(c) A is true but R is false.
(d) A is false but R is true.
36. In the voltage Regulator shown in the figure, the load current can vary from 100 mA to 500 mA . Assuming that the Zener diode is ideal (i.e. Zener Knee current is negligibly small and Zener Resistance is zero in the breakdown Region), the value of ' $R$ ' is.

(a) $7 \Omega$
(b) $70 \Omega$
(c) $70 / 3 \Omega$
(d) $14 \Omega$

(a) photovoltaic effect
(b) photo-conductive effect
(c) photo-electric effect
(d) photo-thermal effect
37. Which one of the following statements is not correct in respect of a series transistor feedback voltage regulator ?
(a) The regulation factor can be improved by increasing the $\mathrm{h}_{\mathrm{fe}}$ of the shunt transistor
(b) The regulation factor can be improved by increasing the resistance between the collector of the shunt transistor and the collector of the series transistor
(c) Output resistance can be reduced by using a Darlington pair in place of the series transistor
(d) Output resistance can be reduced by reducing the $\mathrm{h}_{\mathrm{fe}}$ of the shunt transistor
38. Consider the following circuit :


For the circuit shown above, which one of the following is a correct statement?
(a) $D_{2}$ does not conduct for any value of $V_{i}$
(b) $\mathrm{V}_{0}=10 \mathrm{~V}$ for all values of $\mathrm{V}_{\mathrm{i}}>10 \mathrm{~V}$
(c) $\mathrm{V}_{0}=0 \mathrm{~V}$ for all values of $\mathrm{V}_{\mathrm{i}}<0 \mathrm{~V}$
(d) $\mathrm{V}_{0}=10 \mathrm{~V}$ for all values of $\mathrm{V}_{\mathrm{i}}>0 \mathrm{~V}$
43. The peak current through the resistance in the circuit shown is

(a) 18 mA
(b) 12 mA
(c) 8 mA
(d) 4 mA
44. For the circuit shown in the figure, which one of the following waveforms represents the correct output?

(a)

(b)

(c)

(d)

45. The Zener diode in the regulator circuit shown in the figure has a Zener Voltage of 5.8 volts and a Zener Knee current of 0.5 mA . The maximum load current drawn form this circuit ensuring proper functioning over the input voltage range between 20 and 30 volts, is

(a) 23.7 mA
(b) 14.2 mA
(c) 13.7 mA
(d) 24.2 mA
46. Assume that $\mathrm{D}_{1}$ and $\mathrm{D}_{2}$ in figure are ideal diodes the value of current $I_{s}$ is

(a) 0 mA
(b) 0.5 mA
(c) 1 mA
(d) 2 mA
47. Two p-n junction diodes are connected back to back to make a transistor. Which one of the following is correct?
(a) The current gain of such a transistor will be high
(b) The current gain of such a transistor will be moderate
(c) It cannot be used as a transistor due to large base width
(d) It can be used only for pnp transistor
48. In a p-type silicon sample, the hole concentration is $2.25 \times 10^{15} / \mathrm{cc}$. If the intrinsic carrier concentration is $1.5 \times 10^{10} / \mathrm{cc}$, what is the electron concentration in the p-type silicon sample
(a) zero
(b) $10^{10} / \mathrm{cc}$
(c) $10^{5} / \mathrm{cc}$
(d) $1.5 \times 10^{25} / \mathrm{cc}$
49. What is the reverse recovery time of a diode when switched from forward bias $V_{F}$ to reverse bias $\mathrm{V}_{\mathrm{R}}$ ?
(a) Time taken to remove the stored minority carriers
(b) Time taken by the diode voltage to attain zero value
(c) Time to remove stored minority carriers plus the time to bring the diode voltage to reverse bias $V_{R}$.
(d) Time taken by the diode current to reverse.
50. When a voltage divider biased amplifier has its Q-point near to the middle of the dc-load line, what is the maximum undipped peak-to-peak output voltage?
(a) $\mathrm{V}_{\text {CEQ }}$
(b) $\mathrm{I}_{\mathrm{CQ}} \mathrm{r}_{\mathrm{L}}$
(c) ${ }^{21}{ }_{C Q}{ }^{r_{L}}$
(d) $2 \mathrm{~V}_{\text {CEQ }}$

## ANSWERS AND EXPLANATIONS

1. From the given problem


$$
\begin{aligned}
\mathrm{V}_{0} & =\mathrm{V}_{\mathrm{Z}}=10 \mathrm{~V} \\
\mathrm{I}_{\mathrm{Z} \min } & =25 \mathrm{~mA}
\end{aligned}
$$

$$
I=\left(\frac{20-10}{R}\right)
$$

But $\quad \mathrm{I}_{\mathrm{L}}=\frac{\mathrm{V}_{\mathrm{o}}}{100}=\frac{\mathrm{V}_{\mathrm{z}}}{100}=\frac{10}{100}$

$$
\mathrm{I}_{\mathrm{L}}=100 \mathrm{~mA}
$$

$$
\therefore \quad \mathrm{I}=\mathrm{I}_{\mathrm{z}}+\mathrm{I}_{\mathrm{L}}=125 \mathrm{~mA}
$$

$$
\mathrm{R}=\frac{10}{\mathrm{I}}=\frac{10}{125 \times 10^{-3}}=80 \Omega
$$

2. Ans. (b)

3. Ans. (a)


During +ve half cycle $D_{2}$ acts as voltage regulator.
$\mathrm{D}_{1}$ acts as a PN diode short circuited during Forward bias.
When $\mathrm{i} / \mathrm{p}$ applied $>4.1 \mathrm{~V} \mathrm{D}_{2}$ starts conducting.



Similarly during negative cycle $\mathrm{D}_{1}$ acts as voltage regulator, $D_{2}$ is Forward biased.

4. Ans. (c)

$$
\mathrm{I}_{\mathrm{in}}=\frac{9-6}{50}=0.06 \mathrm{~A}=60 \mathrm{~mA}
$$

Maximum current through the Zener diode is
$\frac{300 \times 10^{-3}}{6}=50 \mathrm{~mA}$
Minimum current through the load is $60-50=$ 10 mA

Maximum current through the load is $60-5=$ 55 mA

Email:info@engineersacademy.org Website : www.engineersacademy.org
5. Ans. (d)

A four diode bridge Rectifier uses smaller size transformer with no center tap and and suitable for high voltage applications.
6. Ans. (b)

Given No-load voltage $=30 \mathrm{~V}$
full-load voltage $=25 \mathrm{~V}$
full-load current $=1 \mathrm{~A}$
Regulation $=\frac{\text { No load }- \text { full load }}{\text { full load }}$

$$
=\frac{30-25}{25}=\frac{1}{5}=20 \%
$$

Output Resistance $=\frac{\text { full load nvoltage }}{\text { full load current }}$

$$
=\frac{25}{1}=25 \Omega
$$

7. Ans. (a)
8. Ans. (b)

When temperature increases the current passing through the diode increases. But to maintain the carrying current as constant, voltage across the diode must be decreased.
9. Ans. (d)
10. Ans. (a)
11. Ans. (c)
12. Ans. (c)
13. Ans. (b)
$\mathrm{R}_{\mathrm{ac}}=\frac{\text { Change in voltage across diode }}{\text { Change in current through diode }}=\frac{\mathrm{dv}}{\mathrm{dI}_{\mathrm{D}}}$
Diff. eq. w.r.t V

$$
\begin{aligned}
& \frac{d v}{{d I_{D}}^{d}}=\mathrm{I}_{\mathrm{s}} \cdot \mathrm{e}^{\frac{\mathrm{V}}{\mathrm{~V}_{\mathrm{T}}}} \cdot \frac{1}{\mathrm{~V}_{\mathrm{T}}}=\frac{\mathrm{I}_{\mathrm{D}}}{\mathrm{~V}_{\mathrm{T}}} \\
\therefore \quad & \mathrm{R}_{\mathrm{ac}}=\frac{\mathrm{V}_{\mathrm{T}}}{\mathrm{I}_{\mathrm{D}}}=\frac{25 \times 10^{-3}}{2 \times 10^{-3}}=12.5 \Omega
\end{aligned}
$$

14. Ans. (a)
15. Ans. (c)

Given $V_{z}=9.5 \mathrm{~V}$,
$\mathrm{V}_{\mathrm{BE}}=0.3 \mathrm{~V}, \beta=99$


$$
\begin{align*}
\mathrm{I}_{1 \max } & =\frac{\mathrm{V}_{\text {in max }}-\mathrm{V}_{\mathrm{o}}}{20}=\frac{30-10}{20}=1 \\
\mathrm{I}_{1 \max } & =1 \mathrm{~A} \\
\mathrm{I}_{\mathrm{E}} & =\mathrm{I}_{\mathrm{C}}+\mathrm{I}_{\mathrm{B}}  \tag{1}\\
\mathrm{I}_{\mathrm{B}} & \left.=\mathrm{I}_{\mathrm{Z}} \text { (when no current flows in } \mathrm{R}_{\mathrm{B}}\right) .
\end{align*}
$$

Then $\beta=\frac{\mathrm{I}_{\mathrm{C}}}{\mathrm{I}_{\mathrm{B}}}=\frac{\mathrm{I}_{\mathrm{C}}}{\mathrm{I}_{\mathrm{Z}}}$

$$
\mathrm{I}_{\mathrm{C}}=\beta \mathrm{I}_{\mathrm{Z}}
$$

$$
\therefore \quad \mathrm{I}_{\mathrm{E}}=\beta \mathrm{I}_{\mathrm{Z}}+\mathrm{I}_{\mathrm{B}}=\beta \mathrm{I}_{\mathrm{Z}}+\mathrm{I}_{\mathrm{Z}} \quad\left[\because \mathrm{I}_{\mathrm{B}}=\mathrm{I}_{\mathrm{Z}}\right]
$$

$$
I_{E}=(\beta+1) I_{Z}=(99+1) I_{Z}[\because \beta=99 \text { given }]
$$

$$
\mathrm{I}_{\mathrm{E}}=100 \times \mathrm{I}_{\mathrm{Z}}
$$

$$
\mathrm{I}_{1}=\mathrm{I}_{\mathrm{E}}=100 \times \mathrm{I}_{\mathrm{Z}}
$$

$$
I_{Z}=\frac{I_{1}}{100}=\frac{1}{100}=0.01 \mathrm{~A}
$$

$$
\mathrm{P}_{\mathrm{Z}}=\mathrm{V}_{\mathrm{Z}} \mathrm{I}_{\mathrm{Z}}
$$

$$
=9.5 \times 0.01\left(\nabla \mathrm{~V}_{\mathrm{z}}=9.5 \text { given }\right)
$$

$$
=95 \mathrm{~mW}
$$

$$
\mathrm{I}_{\mathrm{C}}=\beta \mathrm{I}_{\mathrm{Z}}
$$

$$
=99 \mathrm{I}_{\mathrm{Z}}=99 \times 0.01=0.99 \mathrm{~A}
$$

$$
\mathrm{P}_{\mathrm{T}} \text { (or) } \mathrm{P}_{\mathrm{C}}=\mathrm{V}_{\mathrm{C}} \mathrm{I}_{\mathrm{C}}
$$

$$
=10 \times 0.99=9.9 \mathrm{~W}
$$

16. Ans. (b)
17. Ans. (d)

A is wrong because avalanche breakdown takes place due to a large no. of breaking of covalent bonds across the junction due to impact ionization due to highly energetic electron collision.
18. Ans. (b)

Both are correct since operating point for class A amplifier is at the middle of dc load line so as for whole cycle of $\mathrm{i} / \mathrm{p}$ it work in linear range of transistor so as to work as amplifier so having characteristic like $y=k x$ where $y$ is $o / p$ and $x$ is $\mathrm{i} / \mathrm{p}$ so at the $\mathrm{o} / \mathrm{p}$ frequencies at $\mathrm{i} / \mathrm{p}$ will be present. But R is not the region for A .
19. Ans. (b)

In case of F.b. photo diode it is sensitive to incident light and behave as a normal diode so diode current remains same irrespective of intensity of incident light.
20. Ans. (a)
21. Ans. (d)
22. Ans. (b)
23. Ans. (a)


$$
\mathrm{I}_{1}=\frac{\mathrm{V}_{\mathrm{in}}-\mathrm{V}_{\mathrm{o}}}{\mathrm{R}} \geq \mathrm{I}_{\mathrm{Z}}+\mathrm{I}_{\mathrm{L}}
$$

Given $\mathrm{I}_{\mathrm{Z}}=1 \mathrm{~mA}, \mathrm{I}_{\mathrm{L}}=10 \mathrm{~mA}$
If $\quad V_{\text {in }}=30 \mathrm{~V}$

$$
\begin{align*}
& \mathrm{I}_{1}=\frac{30-10}{\mathrm{R}} \geq(10+1) \mathrm{mA}=\frac{20}{\mathrm{R}} \geq 11 \times 10^{-3} \\
& \mathrm{R} \leq 1818 \Omega  \tag{1}\\
& \text { If } \mathrm{V}_{\text {in }}=50 \mathrm{~V} \\
& \mathrm{I}_{1}=\frac{50-10}{\mathrm{R}} \geq(10-1) \mathrm{mA}=\frac{40}{\mathrm{R}} \geq 11 \times 10^{-3}
\end{align*}
$$

Email : info@engineersacademy.org Website : www.engineersacademy.org
$\mathrm{i}(\mathrm{t})=\frac{\mathrm{V}_{\mathrm{i}}}{50}, \mathrm{i}(\mathrm{t})=\frac{\mathrm{V}_{\mathrm{m}}}{50} \sin \omega \mathrm{t}$
DC component is

$$
\mathrm{Id}_{\mathrm{C}}=\left(\frac{\mathrm{V}_{\mathrm{m}}}{\frac{50}{\pi}}\right)=\left(\frac{\mathrm{V}_{\mathrm{m}}}{50 \pi}\right)
$$

During negative half cycle, D-R.B - replaced by O.C

$$
\Rightarrow \quad \mathrm{I}=0
$$

26. Ans. (c)

The given circuit can be redrawn as


During the positive half cycle of the $\mathrm{i} / \mathrm{p}$ then
$\mathrm{D}_{1} \& \mathrm{D}_{3}-\mathrm{ON}, \rightarrow$ S.C
$D_{2} \& D_{4}-O f f-O . C$

$$
\begin{aligned}
\mathrm{i}(\mathrm{t}) & =\frac{\mathrm{v}(\mathrm{t})}{\mathrm{R}}=\frac{200 \sin \omega \mathrm{t}}{50} \\
& =4 \sin \omega \mathrm{t} . \mathrm{Amp}
\end{aligned}
$$

During the negative half cycle of the input,
$\mathrm{D}_{1} \& \mathrm{D}_{3}-$ off $\rightarrow \mathrm{O} . \mathrm{C}$
$\mathrm{D}_{2} \& \mathrm{D}_{4}-\mathrm{ON} \rightarrow \mathrm{S.C}$


$$
i(t)=\frac{v(t)}{R}=4 \sin \omega t
$$

When $\mathrm{V}_{\mathrm{i}}=-10 \mathrm{~V}$ (max.value)

$$
\begin{gathered}
\mathrm{I}=\frac{-6}{20} \mathrm{~mA}, \mathrm{~V}_{0}+4-10 \mathrm{I}=0 \\
\mathrm{~V}_{0}=10 \mathrm{I}-4=10\left(\frac{-6}{20}\right)-4 \\
=-3-4 \Rightarrow \mathrm{~V}_{0}=-7 \mathrm{~V}
\end{gathered}
$$

32. Ans. (c)
33. Ans. (a)
34. Ans. (d)

High pass RC circuit $\rightarrow$ act as differentiator for low RC.
Low pass RC circuit $\rightarrow$ act as integrator for high RC (time constant)
Clamping circuit act as DC inserter or DC restorer. Clipping circuit act as comparator $\rightarrow$ as it compares $\mathrm{i} / \mathrm{p}$ wrt certain DC voltage and clips off the portion accordingly.
35. Ans. (a)
36. Ans. (d)

$$
\frac{\mathrm{V}_{\mathrm{in}}-\mathrm{V}_{\mathrm{Z}}}{\mathrm{R}} \geq \mathrm{I}_{\mathrm{L}}+\mathrm{I}_{\mathrm{Z}}, \frac{12-5}{\mathrm{R}} \geq \mathrm{I}_{\mathrm{L}}
$$

$$
\left[\because \mathrm{I}_{\mathrm{Z}}=0 \text { given }\right]
$$

where $\mathrm{I}_{\mathrm{L}}=100 \mathrm{~mA}$

$$
\frac{12-5}{\mathrm{R}} \geq 100 \mathrm{~mA}, \frac{7 \times 100}{100} \geq \mathrm{R}
$$

$$
\therefore \mathrm{R}<=70 \Omega
$$

where $\mathrm{I}_{\mathrm{L}}=500 \mathrm{~mA}$

$$
\begin{aligned}
& \frac{12-5}{\mathrm{R}} \geq 500 \mathrm{~mA}, \frac{7 \times 100}{500} \geq \mathrm{R} \\
& \therefore \mathrm{R}<=14 \Omega
\end{aligned}
$$

Take minimum value i.e., $\mathrm{R}=14 \Omega$
37. Ans. (c)

$$
\begin{gathered}
\mathrm{V}_{\mathrm{dc}}=\mathrm{I}_{\mathrm{dc}} \cdot \mathrm{R}_{\mathrm{L}} \\
\quad\left(\therefore \mathrm{~V}_{\mathrm{dc}} \text { in Full Wave Rectifier }\right) \\
=\frac{2 \mathrm{I}_{\mathrm{m}}}{\pi} \cdot \mathrm{R}_{\mathrm{L}}\left(\because \mathrm{I}_{\mathrm{dc}}=\frac{2 \mathrm{I}_{\mathrm{m}}}{\pi}\right), \mathrm{V}_{\mathrm{dc}}=\frac{2 \mathrm{~V}_{\mathrm{m}}}{\pi}
\end{gathered}
$$



PIV in Full Wave Rectifier:
Apply KVL $\mathrm{V}_{\mathrm{m}}+\mathrm{V}_{\mathrm{m}}+\mathrm{V}_{\mathrm{D}}=0$

$$
\mathrm{V}_{\mathrm{D}}=-2 \mathrm{~V}_{\mathrm{m}}
$$

$\therefore \quad$ PIV $=2 \mathrm{~V}_{\mathrm{m}}$
38. Ans. (c)

Given that $\mathrm{V}_{0}=3.5 \mathrm{~V}$

$$
\mathrm{V}_{\mathrm{Z}}=3.3 \mathrm{~V}
$$

Then zener offers

$$
\mathrm{R}_{\mathrm{z}}=\frac{\Delta \mathrm{V}_{0}}{\mathrm{I}_{\mathrm{z}}}
$$

$\mathrm{R}_{\mathrm{z}}=0.1 \mathrm{k} \Omega$ of dynamic resistance.
So $\quad V_{x}+V_{z}=3.5$

$$
\mathrm{I}_{\mathrm{x}}=\left(\frac{3.5-3.3}{\mathrm{R}_{\mathrm{z}}}\right)=2 \mathrm{~mA}
$$

39. Ans. (c)

From the Circuit $\mathrm{D}_{2}$ must be in Forward bias where $\mathrm{D}_{1}$-first replace by O.C
Apply Nodal analysis at
$\frac{\mathrm{V}_{1}-5}{10^{3}}+\frac{\mathrm{V}_{1}+8}{10}=0$


$$
\begin{aligned}
\mathrm{V}_{1}-5+\mathrm{V}_{1}+8 & =0 \\
2 \mathrm{~V}_{1} & =-3 \\
\mathrm{~V}_{1} & =-1.5 \mathrm{~V}
\end{aligned}
$$

$\therefore \mathrm{D}_{1}$ is Reverse biased

$$
\mathrm{I}_{\mathrm{D}_{1}}=0
$$

40. Ans. (b)
41. Ans. (d)
42. Ans. (c)
43. Ans. (c)
44. Ans. (c)
45. Ans. (a)

Given $\mathrm{V}_{\mathrm{i}}=5.8 \mathrm{~V}$
$\mathrm{R}=1 \mathrm{~K}$


The Maximum load current will be
when $\quad V_{i}=V_{\text {max }}=30 \mathrm{~V}$
$\frac{\mathrm{V}_{\text {max }}-\mathrm{V}_{\mathrm{Z}}}{\mathrm{R}} \geq \mathrm{I}_{\mathrm{L}}+\mathrm{I}_{\mathrm{Z}}$
$\frac{30-5.8}{1 k} \geq I_{L}+0.5 \times 10^{-3}$

$$
\frac{24.2}{1 \mathrm{k}} \geq 0.5 \times 10^{-3}+\mathrm{I}_{\mathrm{L}}
$$

$$
\begin{aligned}
24.2 \times 10^{-3} & \geq 0.5 \times 10^{-3}+\mathrm{I}_{\mathrm{L}} \\
\mathrm{I}_{\mathrm{L}} & =23.7 \mathrm{~mA}
\end{aligned}
$$

46. Ans. (a)

The current always selects the low resistance path. $\mathrm{D}_{1}-\mathrm{ON}$ and $\mathrm{D}_{2}$-OFF.
The I directed from N type to $\mathrm{P}-$ type $\left(\mathrm{D}_{2}-\mathrm{R} . \mathrm{B}\right)$
As $\mathrm{D}_{2}-$ R.B replaced by O.C

$$
\therefore \quad \mathrm{I}=0
$$


47. Ans. (c)


This configuration will not work as a transistor because base width will be too large. So that carrier injected from forward biase diode (equivalent to emitter - base junction) will not reach to collector.
48. Ans. (c)

Given that

$$
\begin{aligned}
\mathrm{p} & =2.25 \times 10^{15} / \mathrm{cc} \\
\text { and } \quad \mathrm{n}_{1} & =1.5 \times 10^{10} / \mathrm{cc}
\end{aligned}
$$

According to mass action low

$$
\mathrm{np}=\mathrm{n}_{\mathrm{i}}^{2}
$$

$$
\begin{aligned}
\mathrm{n} & =\frac{\mathrm{n}_{\mathrm{i}}^{2}}{\mathrm{p}}=\frac{\left(1.5 \times 10^{10}\right)^{2}}{2.25 \times 10^{15}} \\
& =10^{5} / \mathrm{cc}
\end{aligned}
$$

49. Ans. (c)


Recovery time $t_{r}=t_{s}+t_{d}$
$\mathrm{t}_{\mathrm{s}}=$ storage time (to remove stored minority
carriers)
$t_{d}=$ to bring the diode in reverse biase condition i.e. $V_{D}=V_{R}$ ) and current $i=0$.
50. Ans. (d)

